

# **Tunable RF and Analog Circuits Using On-Chip MEMS Passive Components**

**Gary K. Fedder<sup>1,2</sup> and Tamal Mukherjee<sup>1</sup>**

***<sup>1</sup>Dept. of Electrical and Computer Engineering***

***<sup>2</sup>The Robotics Institute***

***Carnegie Mellon University***

***Pittsburgh, PA 15213-3890***

**fedder,tamal@ece.cmu.edu**

**http://www.ece.cmu.edu/~mems**

**Funding:**

**DARPA Microsystems Technology Office**

**MARCO/DARPA C2S2, Center for Circuits and Systems Solutions**

***DARPA ASP Proposers Day – November 14, 2005***

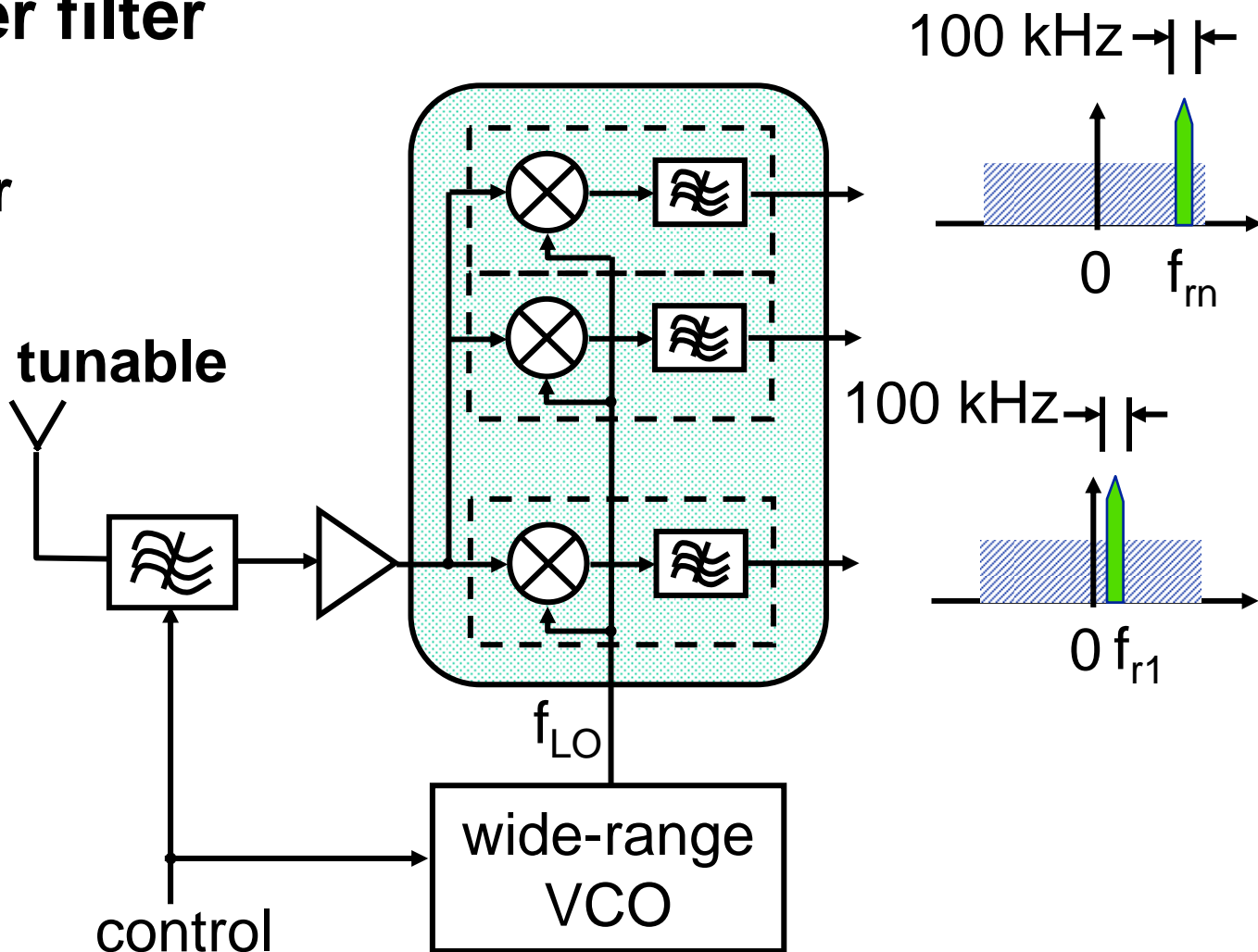
# MEMS Channel Selectable Architecture

## ■ MEMS mixer filter

- High Q
- Low power
- Low area
- Not widely tunable

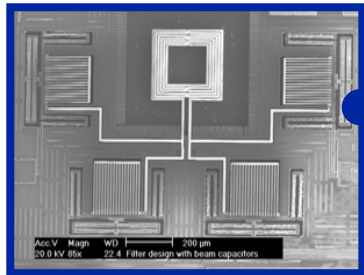
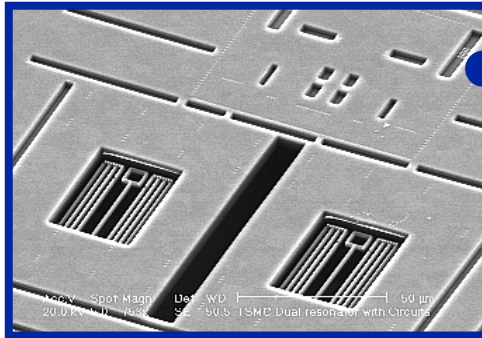
## ■ Mixer filter array

- High Q  
*and*  
channel  
select



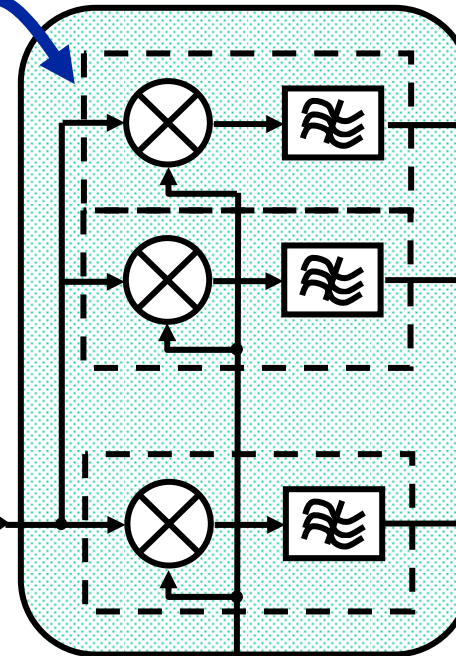
# Integrated RF-MEMS-Enhanced Receivers

**MEMS  
Mixer-  
Filter**



**MEMS-tunable  
Bandpass Filter**

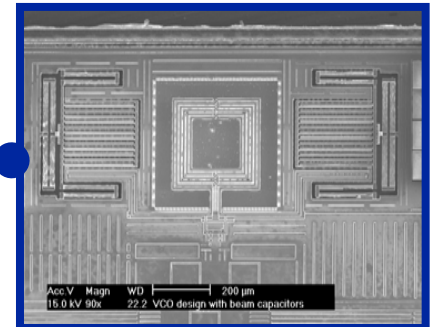
control



ADCs  
&  
digital

**MEMS-tunable VCO**

wide-range  
VCO

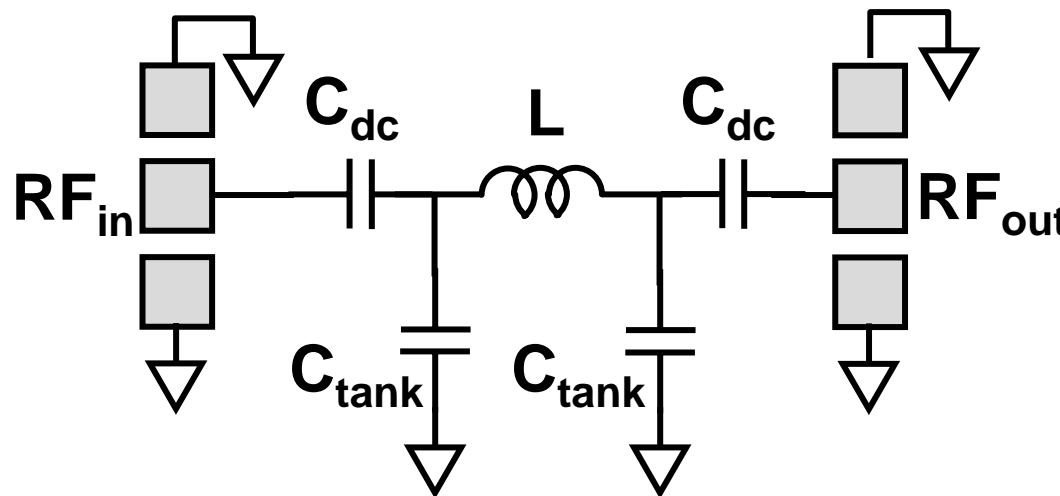


# Reconfigurable Image-Reject Filters

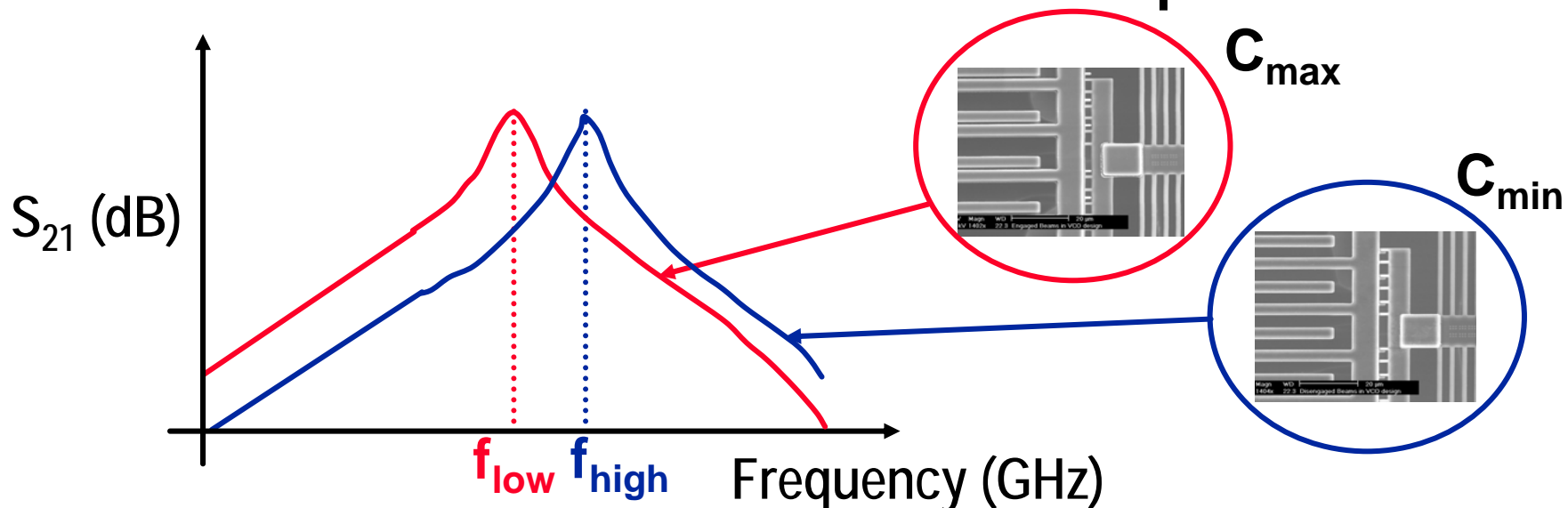
## Initial $\pi$ -Filter design

■  $f_{\text{low}} = 1.7 \text{ GHz}$

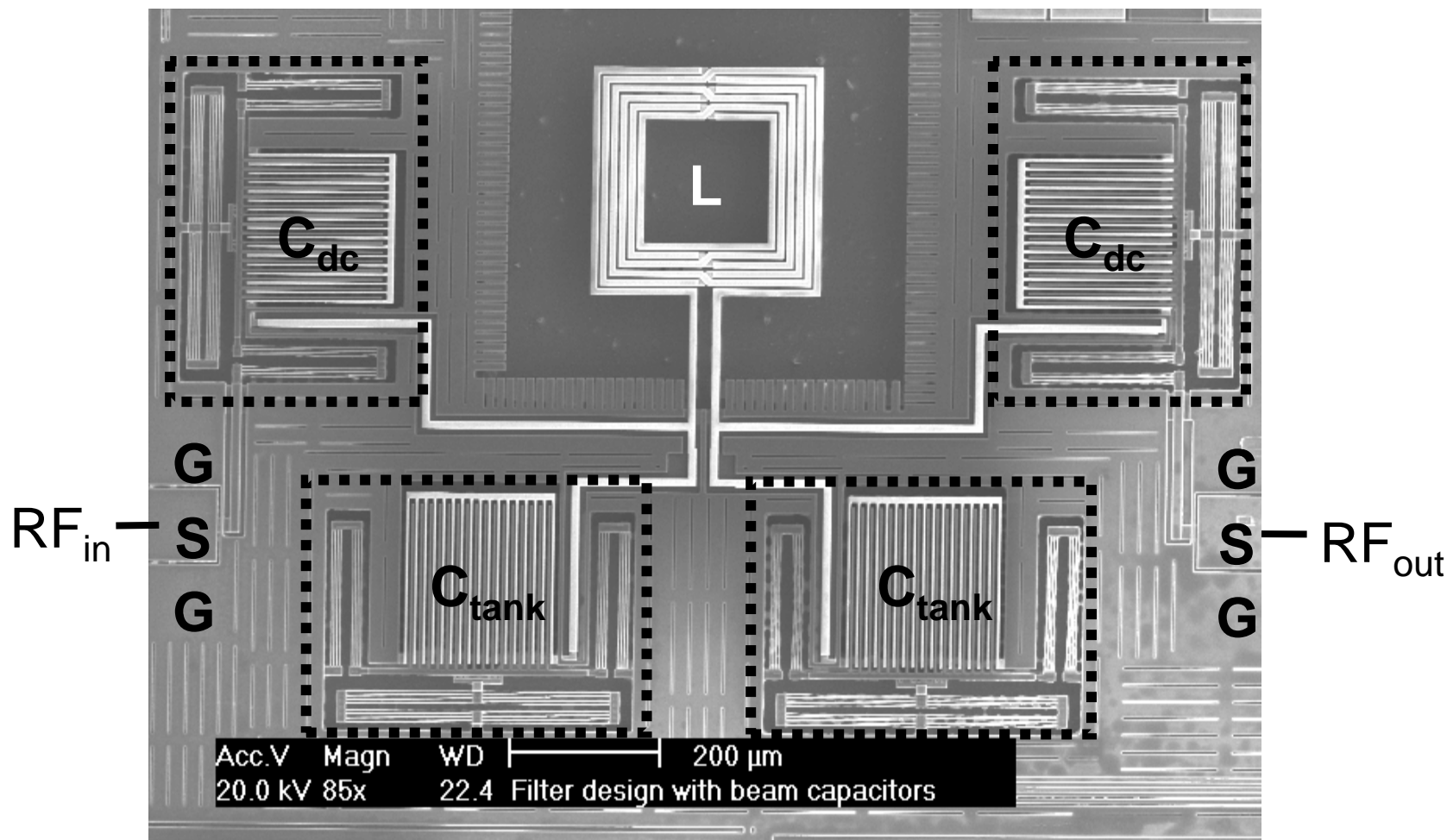
■  $f_{\text{high}} = 2.6 \text{ GHz}$



## Latched RF MEMS capacitive switches



# RF MEMS LC Filter in Jazz SiGe60 BiCMOS



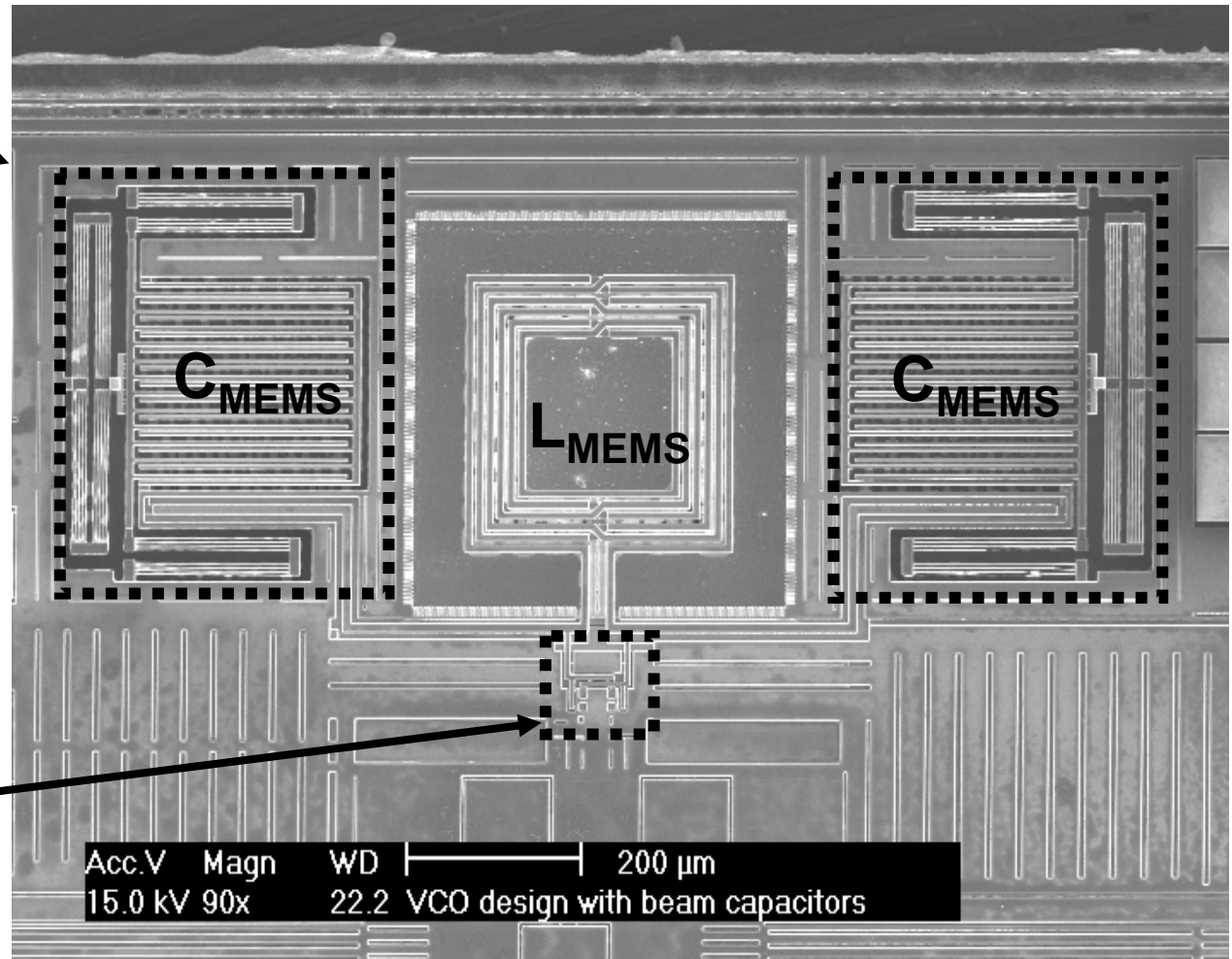
$$250 \text{ fF} < C_{\text{dc}} < 550 \text{ fF}; \quad 300 \text{ fF} < C_{\text{tank}} < 800 \text{ fF}$$

Measured reconfigurable switching range = 850 MHz

# RF MEMS VCO in Jazz SiGe60 BiCMOS

area = 0.87 mm<sup>2</sup>

active circuit



$$L_{\text{MEMS}} = 6.25 \text{ nH}; 180 \text{ fF} < C_{\text{MEMS}} < 1 \text{ pF}$$

$$f_0 = 2.844 \text{ GHz}, 122 \text{ dBc/Hz @ 1 MHz offset \& 2.7 mW}$$

# MEMS Mixer-Filter Principle

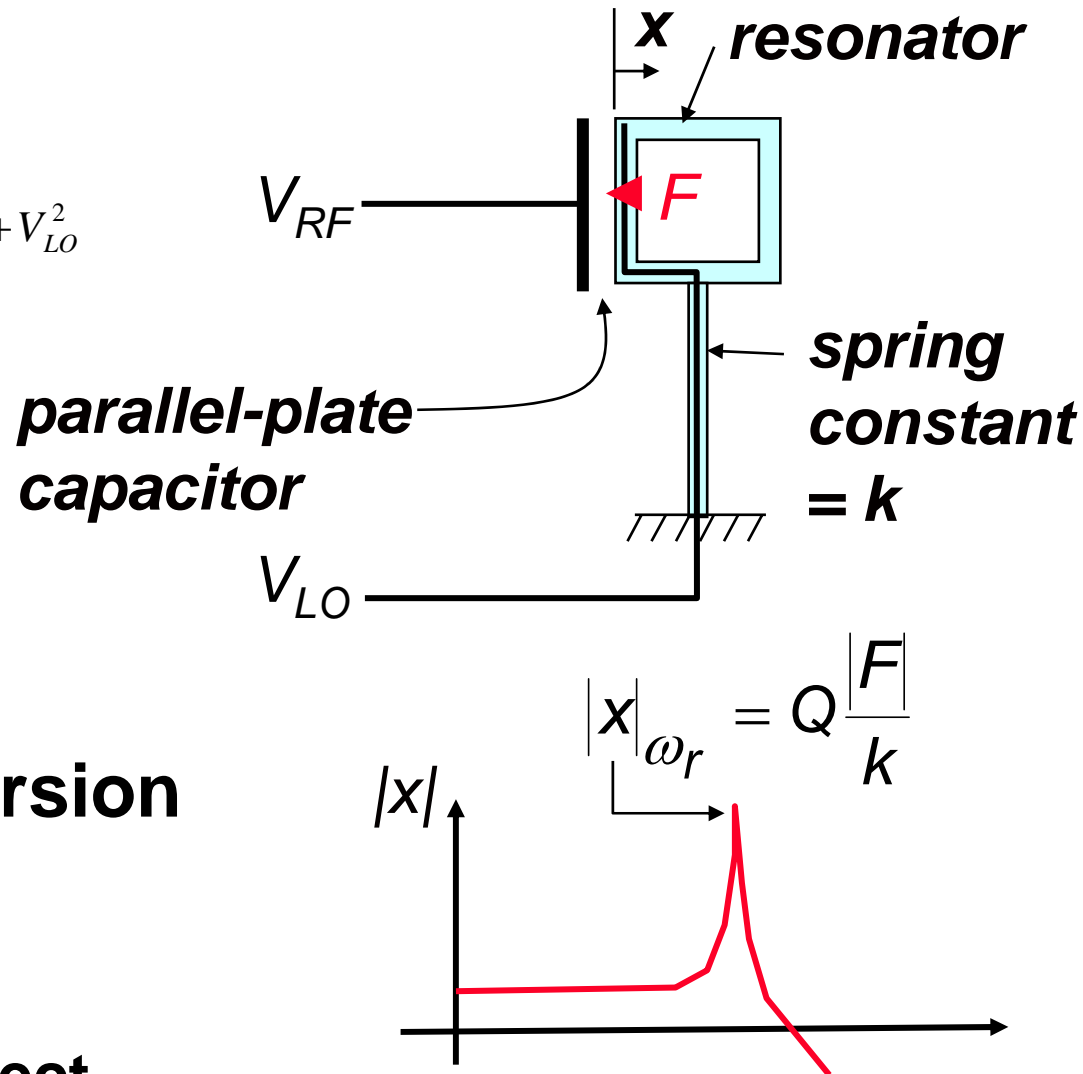
## ■ Electrostatic force works as mixer

$$F = \frac{1}{2} \frac{dC}{dx} (V_{RF} - V_{LO})^2 \propto V_{RF}^2 \underbrace{-2V_{RF}V_{LO}}_{\text{Mixer term}} + V_{LO}^2$$

## ■ Force creates mechanical displacement, $x$

## ■ Direct down conversion of RF to MEMS resonance

### ■ Resonant filter effect





# Mixer-Filter Output

■ DC “polarizing” voltage,  $V_p$ , across output gap

■ Displacement current, proportional to:

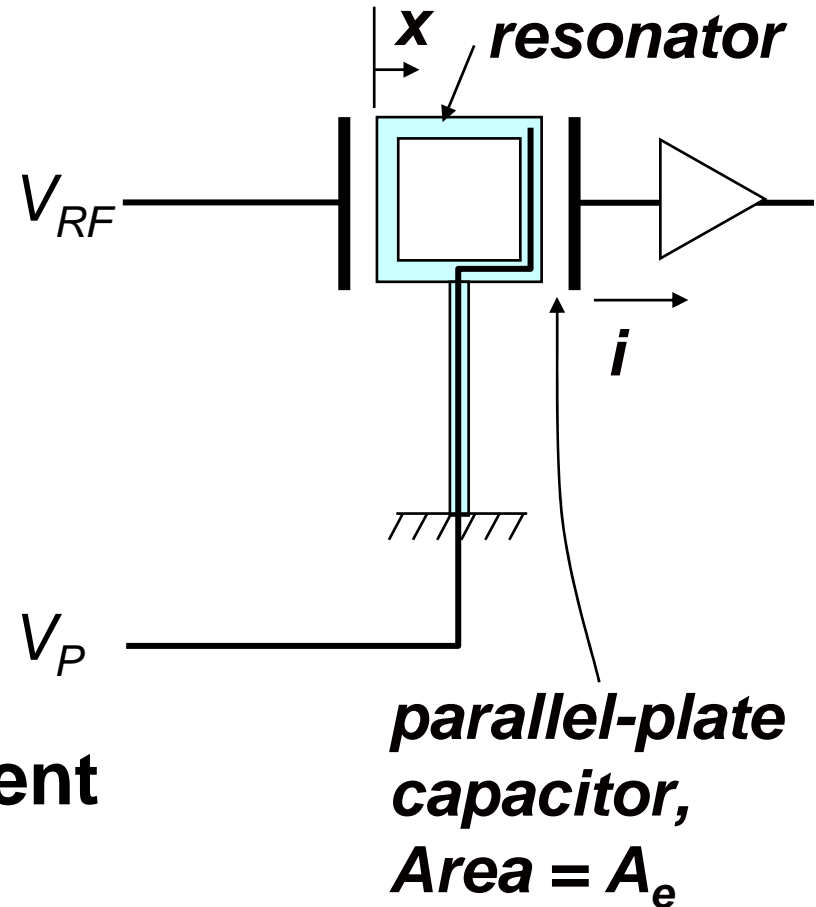
■  $V_p$

■ velocity

■  $V_{LO} \times V_{RF}$

■ Pre-amplifier detects current

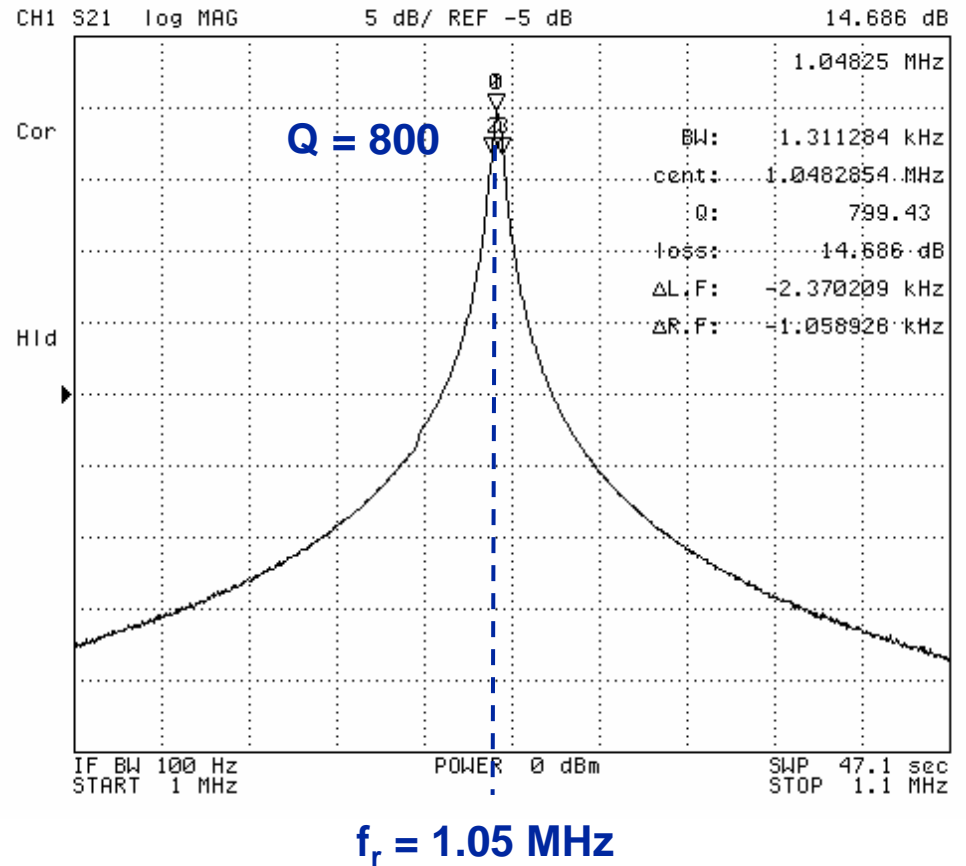
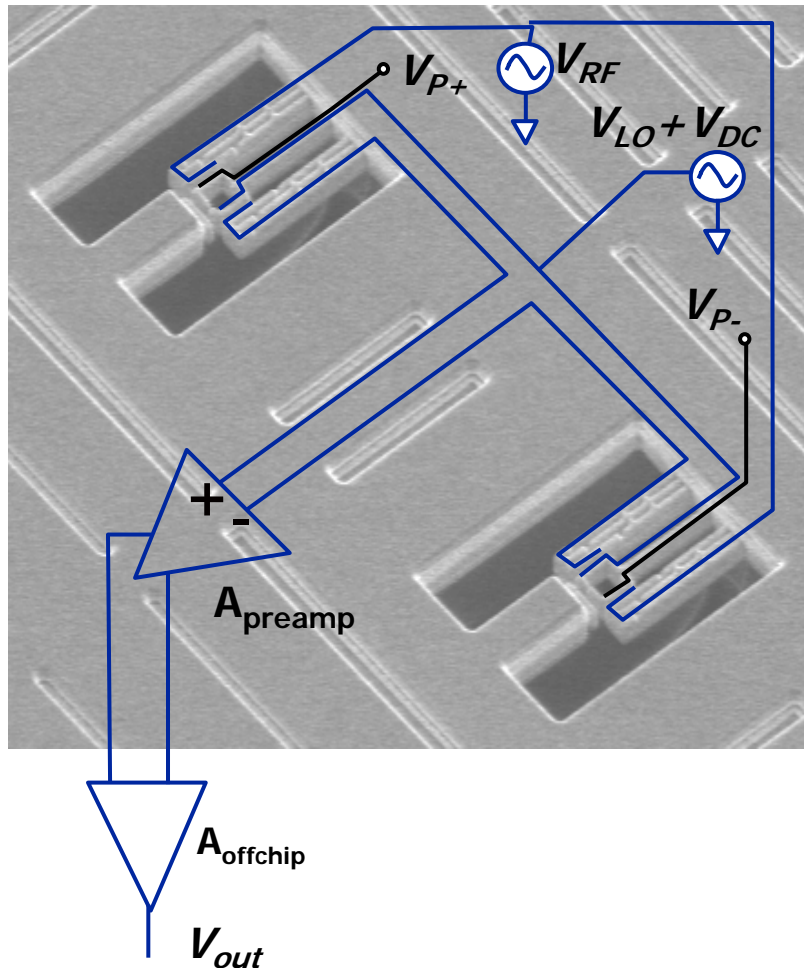
$$|i|_{\omega_r} = V_p \frac{dC}{dx} \frac{dx}{dt} = \frac{k(\epsilon_0 A_e)^2}{2Q\omega_r g^4} V_p V_{LO} V_{RF}$$





# CMOS-MEMS Resonator Q

*in Jazz 0.35  $\mu\text{m}$  CMOS*



# Mixer-Filter Characteristics

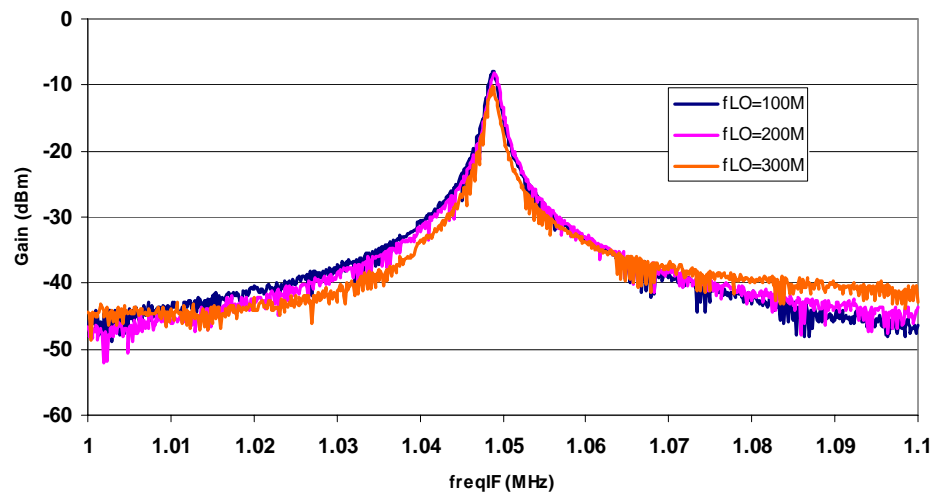
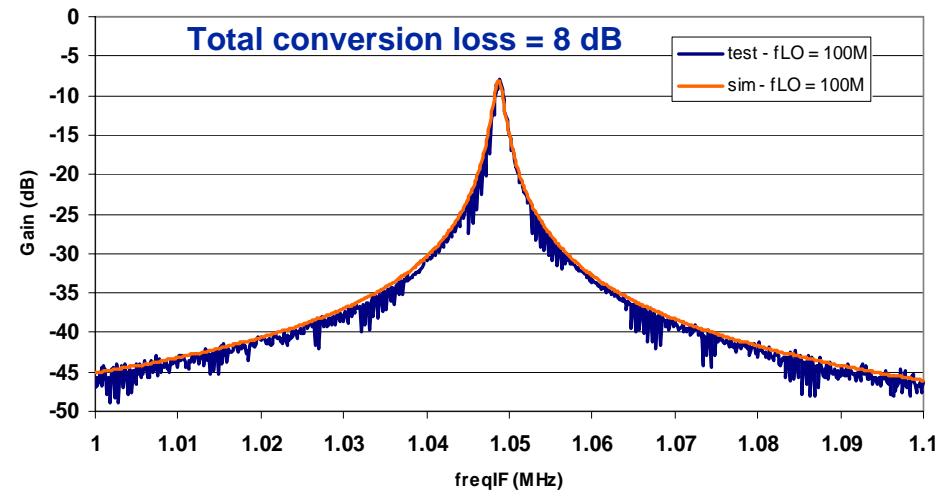
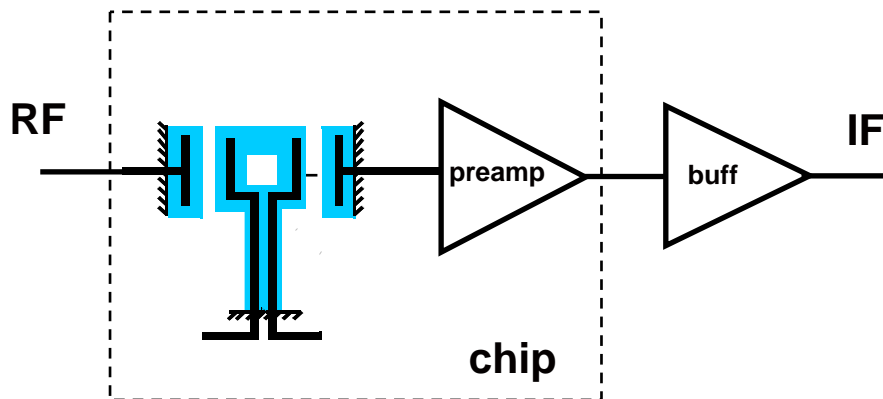
## ■ Inputs:

$$V_{LO} = 1.4 \text{ V (peak)}$$

$$V_{P+} = 10\text{V}, V_{P-} = V_{\text{preamp-}}$$

## ■ LO stepped 10 - 400 MHz

## ■ Measured results are well-matched to simulated results



**The views, opinions, and/or findings contained in this article are those of the author and should not be interpreted as representing the official policies, either expressed or implied, of the Defense Advanced Research Projects Agency or the Department of Defense**